NSN 5962-01-245-3447

Memory Microcircuit - Page 1 of 2



View Online at https://aerobasegroup.com/nsn/5962-01-245-3447

0.975 inches	
Body Width:	
0.300 inches	
Body Height:	
0.180 inches	
Maximum Power Di	ssipation Rating:
550.0 milliwatts	
Operating Tempura	ture Range:
-55.0/+125.0 degrees	s celsius
Storage Tempuratu	re Range:
-65.0/+150.0 degrees	s celsius
Features Provided:	
Hermetically sealed a	and burn in and programmable and schottky and 3-state output
Inclosure Material:	
Ceramic	
Inclosure Configura	ition:
Dual-in-line	
Output Logic Form:	
Transistor-transistor	ogic
Input Circuit Patterr	1:
10 input	
Terminal Surface Tr	eatment:
Solder	
Voltage Rating And	Type Per Characteristic:
7.0 volts power sour	ce
Time Rating Per Ch	acteristic:
70.00 nanoseconds	propagation delay time, low to high level output and 70.00 nanoseconds propagation delay time, high to low leve
output	
Memory Device Typ	e:
Rom	
Memory Capacity:	
Unknown	
Test Data Documen	t:
96906-mil-std-883 sta	andard (includes industry or association standards, individual manufactureer standards, etc.).
Terminal Type And	Quantity:
20 printed circuit	
Shelf Life:	
N/a	
Unit Of Measure:	

Yes - demil/mli

NSN 5962-01-245-3447

Memory Microcircuit - Page 2 of 2

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